

ABSTRACT OF THE DISCLOSURE

A non-volatile semiconductor memory device includes a semiconductor substrate, a memory cell array formed on the semiconductor substrate, and including
5 a first gate insulator having a first thickness. The device further includes a high-voltage transistor circuit formed on the semiconductor substrate, and including a second gate insulator having a second thickness greater than the first thickness, and
10 a peripheral circuit formed on the semiconductor substrate, and including the second gate insulator.